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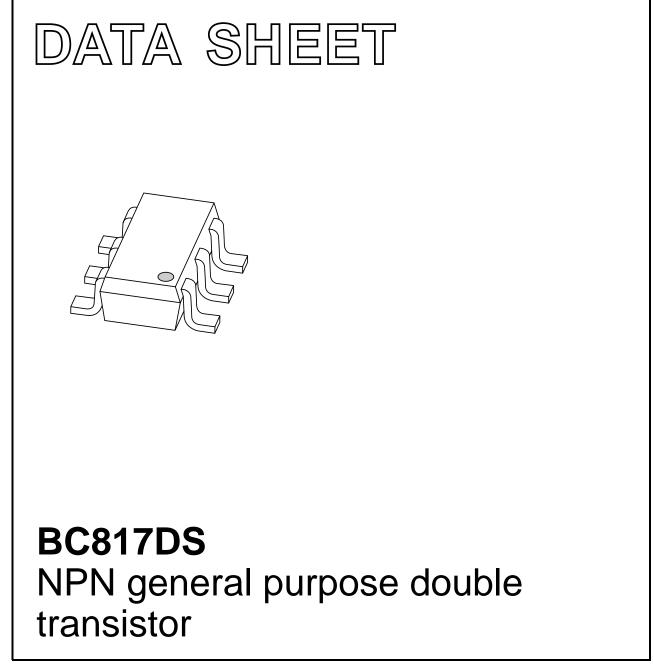
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2002 Aug 09 2002 Nov 22



BC817DS

FEATURES

- High current (500 mA)
- 600 mW total power dissipation
- Replaces two SOT23 packaged transistors on same PCB area.

APPLICATIONS

- · General purpose switching and amplification
- Push-pull amplifiers
- Multi-phase stepper motor drivers.

DESCRIPTION

NPN transistor pair in a SOT457 (SC-74) plastic package.

MARKING

TYPE NUMBER	MARKING CODE			
BC817DS	N3			

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	45	V
I _C	collector current (DC)	500	mA
I _{CM}	peak collector current	1	А

PINNING

PIN	DESCRIPTION	
1, 4	emitter	TR1; TR2
2, 5	base	TR1; TR2
6, 3	collector	TR1; TR2

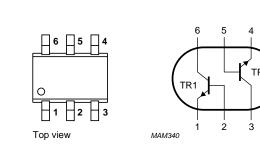


Fig.1 Simplified outline (SOT457) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transi	stor unless otherwise specified				•
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	45	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current (DC)		-	500	mA
I _{CM}	peak collector current		-	1	А
I _{BM}	peak base current		-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \text{ °C}; \text{ note } 1$	-	370	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
Per device	9			•	•
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	600	mW

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	208	K/W

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

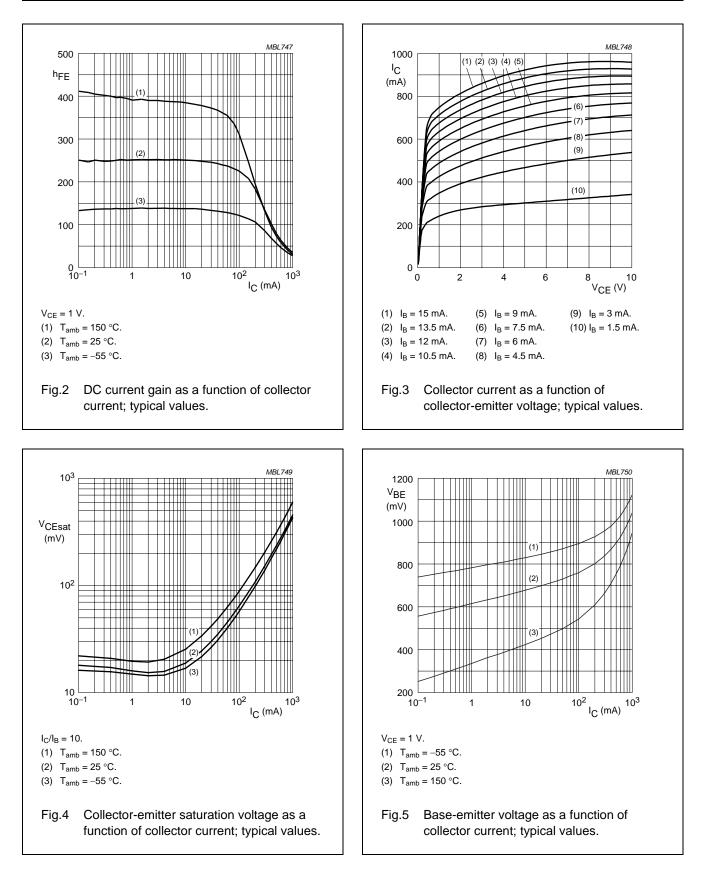
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	Per transistor					
I _{CBO}	collector-base cut-off current	$V_{CB} = 20 \text{ V}; I_E = 0$	—	-	100	nA
		$V_{CB} = 20 \text{ V}; \text{ I}_{E} = 0; \text{ T}_{j} = 150 ^{\circ}\text{C}$	-	_	5	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 V; I_{C} = 0$	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 1 V; I _C = 100 mA; note 1	160	-	400	
		V _{CE} = 1 V; I _C = 500 mA; note 1	40	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 500 mA; I _B = 50 mA; note 1	-	-	700	mV
V_{BE}	base-emitter voltage	$V_{CE} = 1 V; I_C = 500 mA;$ notes 1 and 2	-	-	1.2	V
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	-	5	-	pF
f _T	transition frequency	V _{CE} = 5 V; I _C = 10 mA; f = 100 MHz	100	_	_	MHz

Notes

1. Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

2. V_{BE} decreases by approximately -2 mV/K with increasing temperature.

BC817DS



Product data sheet

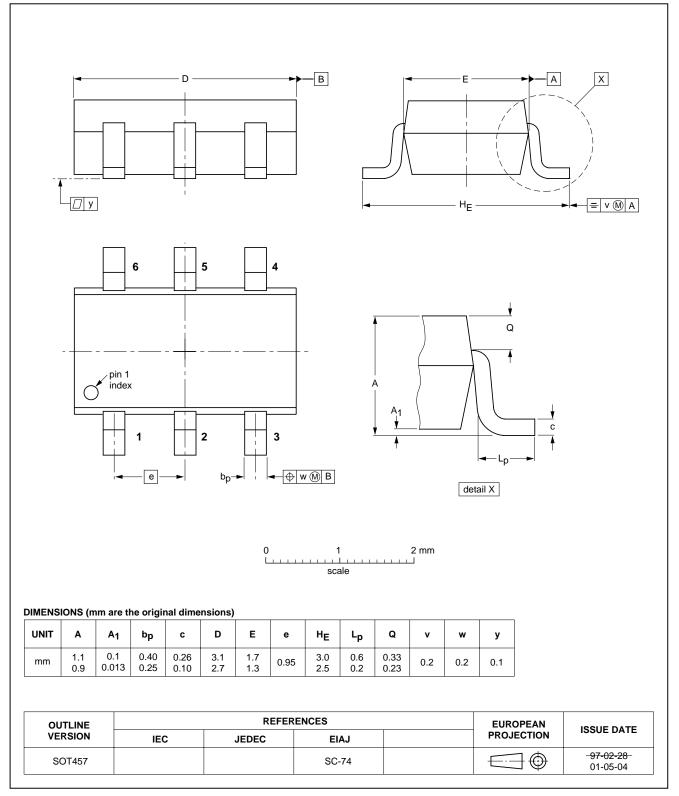
BC817DS

SOT457

NPN general purpose double transistor

PACKAGE OUTLINE





BC817DS

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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NXP Semiconductors

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